



Attorney Docket No. 0756-2367

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Masaaki HIROKI et al.
Serial No. 09/961,055
Filed: September 24, 2001
For: ELECTRO-OPTICAL DEVICE

) Group Art Unit: 2871
) Examiner: Zhi Q. Qi
) CERTIFICATE OF MAILING
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) Commissioner for Patents, P.O. Box 1450,
) Alexandria, VA 22313-1450, on July 13, 2007.

Adrian Stamer

RESPONSE

Honorable Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

The Official Action mailed March 13, 2007, and the Advisory Action mailed June 25, 2007, have been received and their contents carefully noted. This response supplements the *Amendment* filed June 13, 2007. Filed concurrently herewith is a *Request for One Month Extension of Time*, which extends the shortened statutory period for response to July 13, 2007. Also, filed concurrently herewith is a *Request for Continued Examination*, which requests entry of the previously filed *Amendment* of June 13, 2007. Accordingly, the Applicant respectfully submits that this response is being timely filed.

Further to the amendments and remarks set forth in the Amendment filed June 13, 2007, the Examiner's attention is directed to JP 06-032814 submitted with the Information Disclosure Statement filed concurrently herewith. In JP 06-032814, it is disclosed that a resin for an electronic device includes plural impurity ions such as iron (Fe), sodium (Na), potassium (K), and copper (Cu). When using a resin for the electronic device, it is necessary to prevent these impurity ions from the resin from entering a channel region of a transistor. The structure of the subject invention as

recited in all independent claims 6, 7, 9, 39, 40, and 42 can prevent these impurity ions from the resin from entering into the channel region. Because a gate insulating film 954 containing fluorine covers a semiconductor film and is in contact with a top surface and side surfaces of the semiconductor film in the present invention, the gate insulating film can prevent plural impurity ions included in an organic resin film 969 from entering into a channel region of the semiconductor film, as disclosed at page 14, lines 15-20 and Figures 18A to 18F, for example, of the present specification. In addition to the distinctions previously noted, since Tsujikawa, Woods, and Parks, either along or in combination, do not teach or suggest the above feature, the subject application should be in condition for allowance.

Should the Examiner believe that anything further would be desirable to place this application in better condition for allowance, the Examiner is invited to contact the undersigned at the telephone number listed below.

Respectfully submitted,


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